# 2SB1414

### Silicon PNP epitaxial planar type

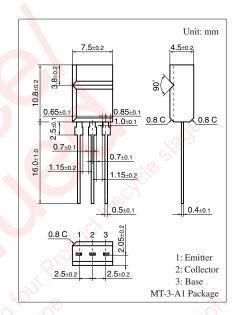
For low-frequency driver/high power amplification Complementary to 2SD2134

#### ■ Features

- ullet Excellent current  $I_C$  characteristics of forward current transfer ratio  $h_{FE}$  vs. collector
- High transition frequency f<sub>T</sub>
- Allowing automatic insertion with radial taping

### ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	-150	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-150	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V	
Collector current	$I_{C}$	-1	A	
Peak collector current	$I_{CP}$	-1.5	A	
Collector power dissipation	P <sub>C</sub>	1.5	W	
Junction temperature	Tj	150	°CO	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



### ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -100 \mu\text{A},  I_B = 0$	-150			V
Emiter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu\text{A},  I_C = 0$	-5			V
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	90		330	_
	h <sub>FE2</sub>	$V_{CE} = -5 \text{ V}, I_C = -500 \text{ mA}$	50			
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.5	-2.0	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		-1.0	-2.0	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ 30		30		pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

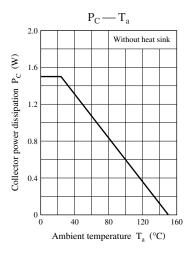
2. \*1: Pulse measurement

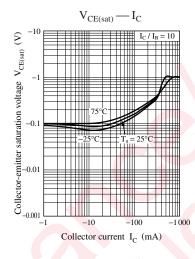
\*2: Rank classification

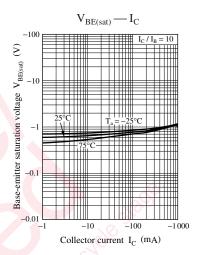
Rank	Q	R	S
h <sub>FE1</sub>	90 to 155	130 to 220	185 to 330

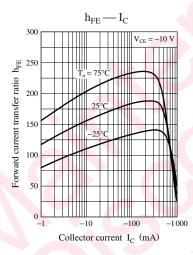
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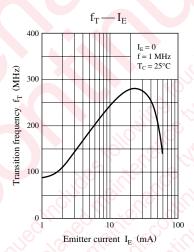
## **Panasonic**

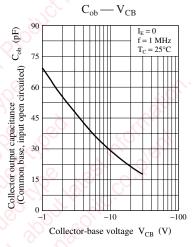


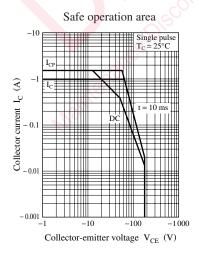


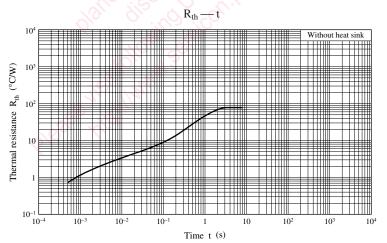












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